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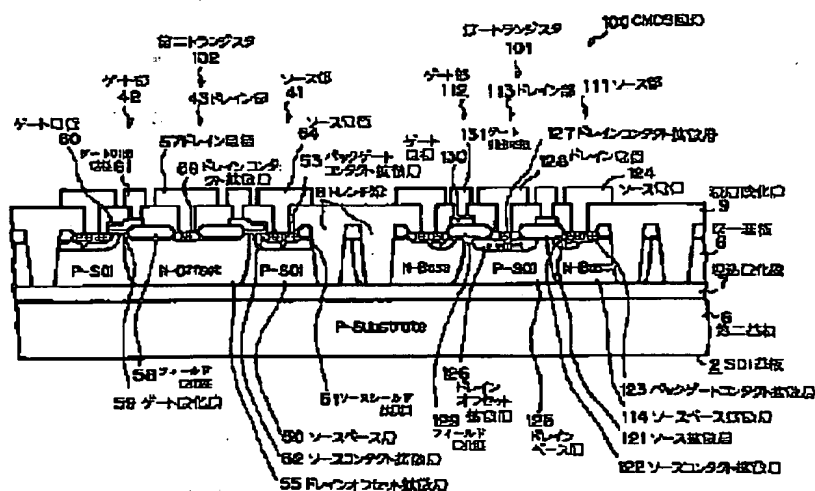
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DEVICE AND ITS
MANUFACTURE****(57) Abstract:**

PROBLEM TO BE SOLVED: To make the breakdown strength and the on-resistance of a pair of transistors equal in a semiconductor device of a CMOS structure, in which a pair of offset-type first conductivity-type and second conductivity-type transistors are formed on one first conductivity-type substrate.

SOLUTION: A second conductivity-type transistor 102 is formed to be of an LMOS structure, and a first conductivity-type transistor 101 is formed to be of an LDMOS structure. Thereby, a drain-base layer 125, whose function is identical to that of a drain offset diffused layer 126, is formed in the position of a substrate 5 separately from a source-base diffused layer 114 in the first conductivity-type transistor 101. The first conductivity-type transistor has a structure, whose breakdown strength is stable and whose ON-resistance is high, in the same manner as the second conductivity-type transistor 102.



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